

ECEN 607 (ESS)

Additional notes on the Flipped Voltage Follower

Courtesy of Prof. Jaime Ramirez-
Angulo

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Local Feedback Loops

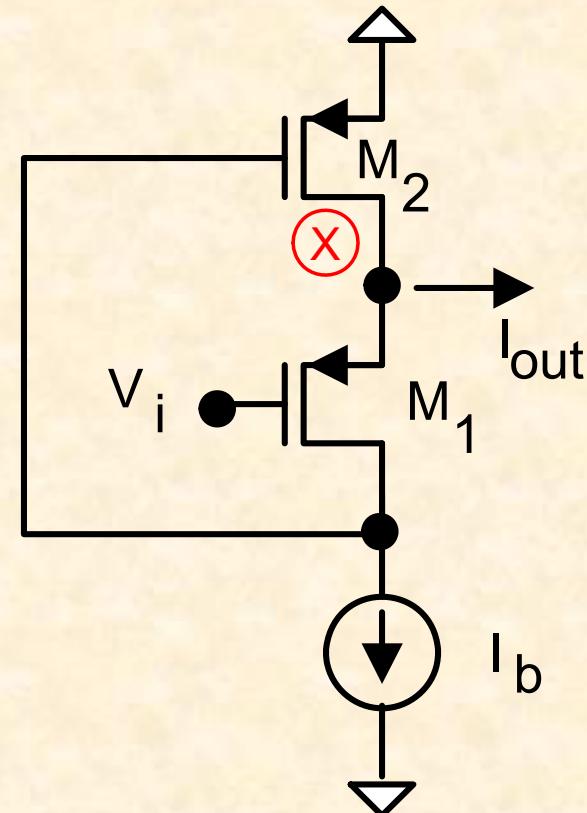
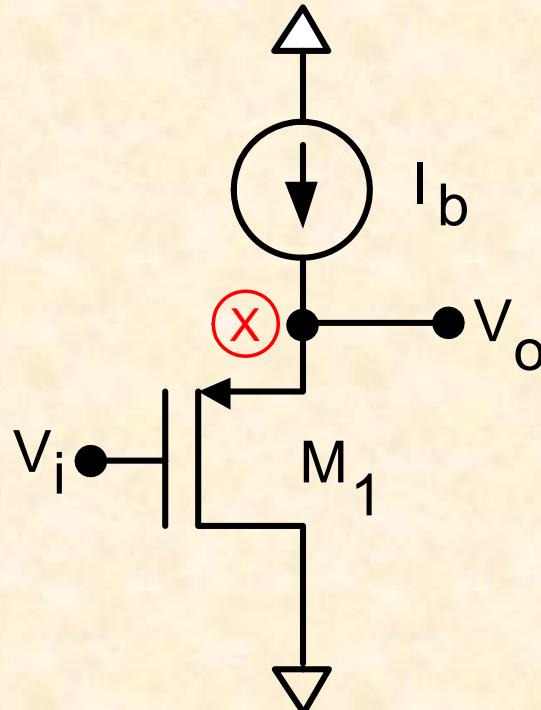
Basic Idea

V. Ivanov, J. Zhou and I.M. Filanovsky, "A 100-dB CMRR CMOS Operational Amplifier With Single-Supply Capability," IEEE Transactions on Circuits and Systems II: Express Briefs, vol. 54, no. 5, May 2007, pp.397-401

- To improve performance of simple transistors:
 - » By adding local feedback loops to:
 - » Decrease/increase impedance levels at certain nodes.
 - » Decrease/increase signal swing at certain nodes.
- Drawbacks:
 - » Feedback always implies stability problems
- Advantages:
 - » Local Feedback is faster and does not require compensation if properly designed.
 - » It allows easy Class AB implementation

Local Feedback Loops

A possible Implementation



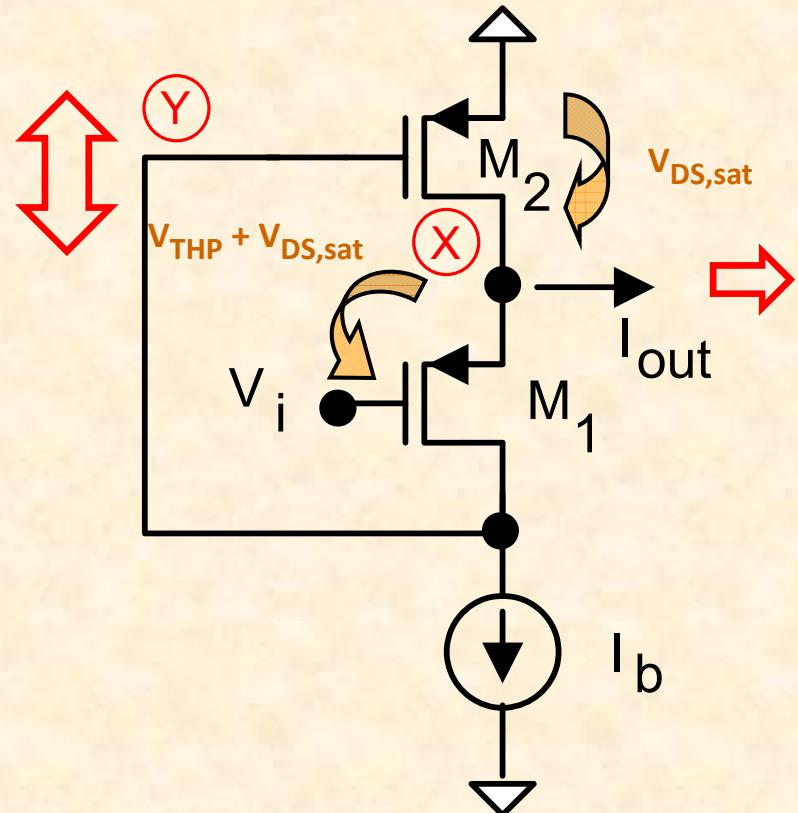
Voltage Follower

Flipped Voltage Follower(FVF)

Local Feedback Loops

Flipped Voltage Follower (FVF)

- V_x is defined by the value of V_i and I_b and follows the variations of V_i
- The circuit is able to source (I_{out}) currents much larger than I_b
- Low impedance at node X
 $R_x = 1/(g_{m2} g_{m1} r_{o1})$



$$V_{DD,min} = |V_{THP}| + 2V_{DS,sat}$$

Local Feedback Loops

Flipped Voltage Follower (FVF)

- It is able to operate with Low-Voltage supply

$$V_{DD}^{MIN} = |V_{TP}| + 2V_{DS,sat}$$

- It features a low impedance node:

$$R_x \approx 1/(g_{m2} g_{m1} r_{o1})$$

- And a high impedance node

$$R_i \approx \infty$$

- There are no stability problems [*]

- It is able to provide a load with currents much larger than the bias current



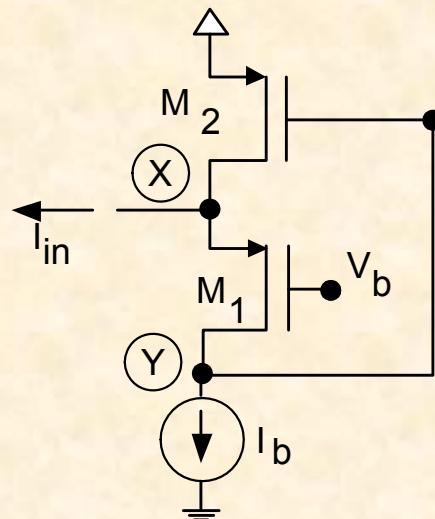
Class-AB

[*] R.G. Carvajal, J. Ramírez-Angulo, A. López-Martin, A. Torralba, J. Galán, A. Carlosena and F. Muñoz, "The Flipped Voltage Follower: A useful cell for low-voltage low-power circuit design," **IEEE Trans. on Circuits and Systems-I**, vol 52, no. 7, Julio 2005.

LFL: Basic Cells

Local Feedback Loops: Class-AB operation

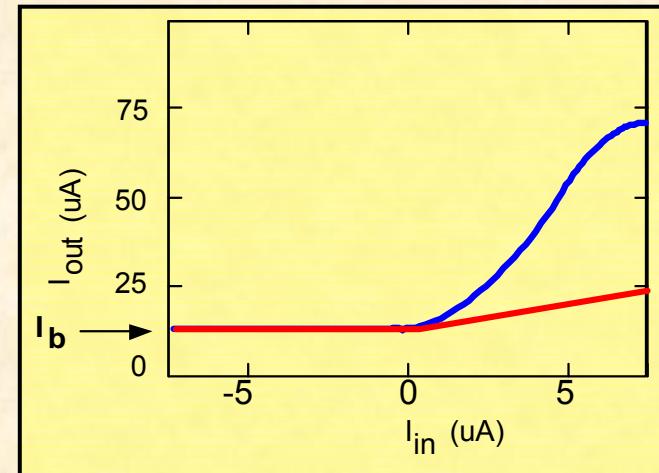
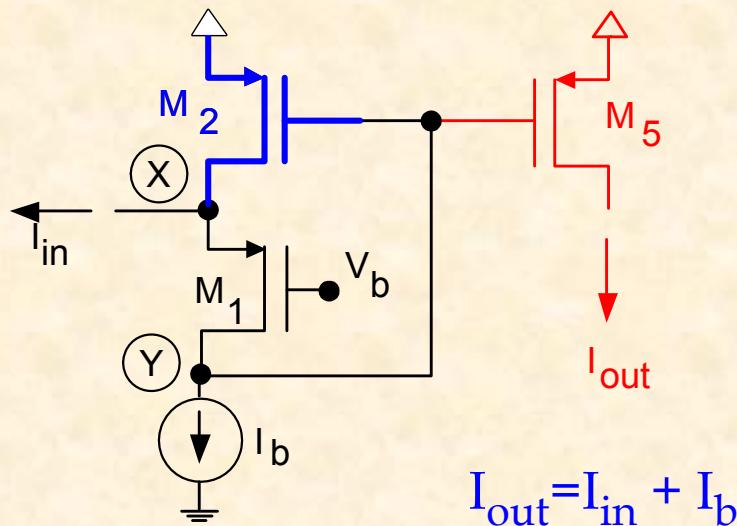
► **Objective:** Design cells for $V_{DD} < V_{DDmin}$ featuring Class-AB behavior



LFL: Basic Cells

Local Feedback Loops: Class-AB operation

► Objective: Design cells for $V_{DD} < V_{DDmin}$ featuring Class-AB behavior

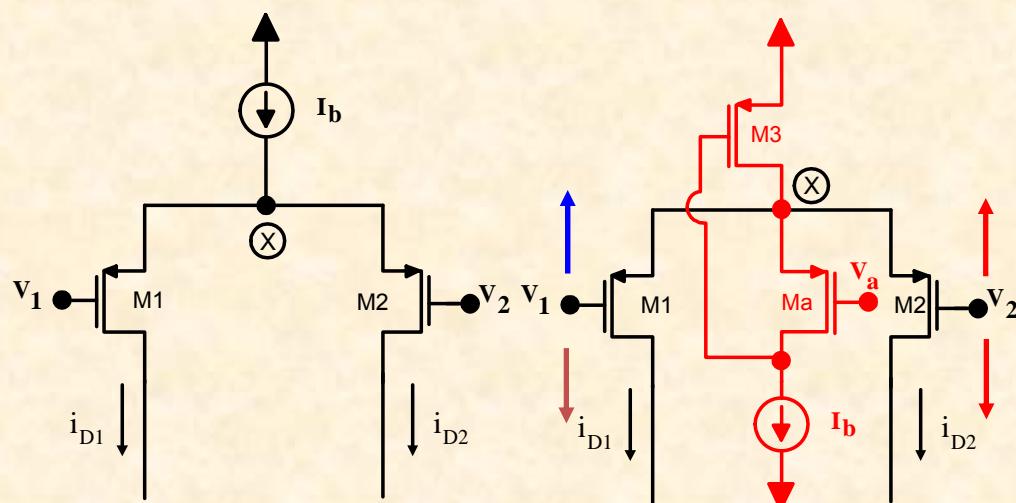


Current Sensing

LFL: Basic Cells

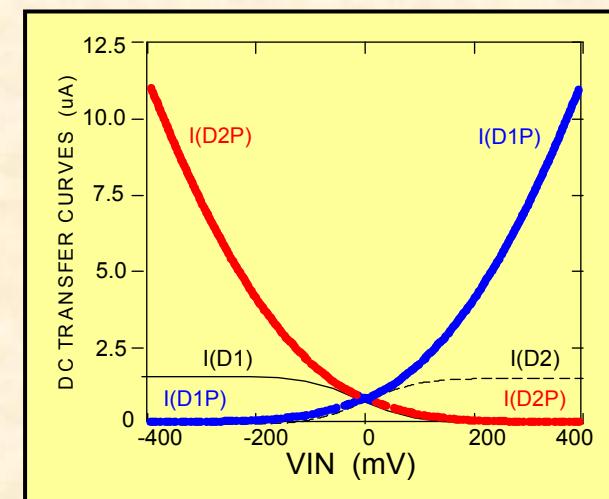
Local Feedback Loops: Class-AB operation

► Objective: Design cells for $V_{DD} < V_{DDmin}$ featuring Class-AB behavior



Class-A
differential pair

Class-AB pseudo
differential pair



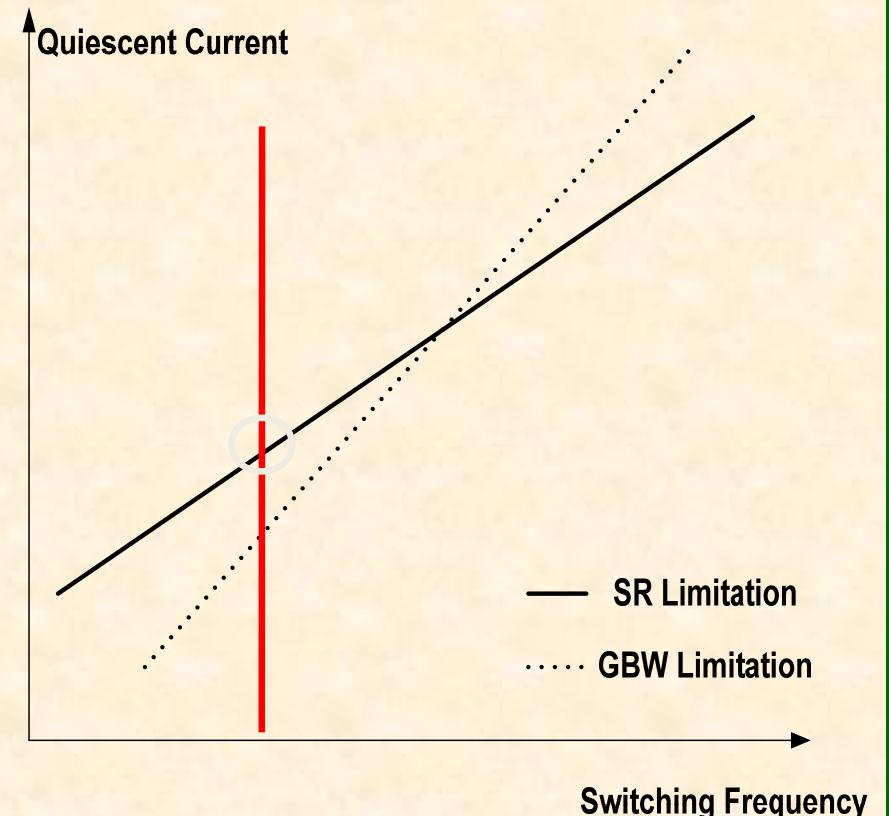
Comparison

LFL: Basic Cells

Local Feedback Loops: Class-AB operation

- ➡ **Objective:** Design cells for $V_{DD} < V_{DDmin}$ featuring Class-AB behavior

- ➡ Quiescent Current in Class-A based SC circuits:
 - ➡ Limits Slew-Rate
 - ➡ Limits GBW
- ➡ Depending on clock freq.:
 - ➡ One of them sets I^Q
 - ➡ For low freq. SR limits.



G. Giustolisi and G. Palumbo, "A novel 1-V class-AB transconductor for improving speed performance in SC applications,". **ISCAS 2003**, vol. 1, 25-28 May 2003 pp. 153-156

LFL: Basic Cells

Local Feedback Loops: Class-AB operation

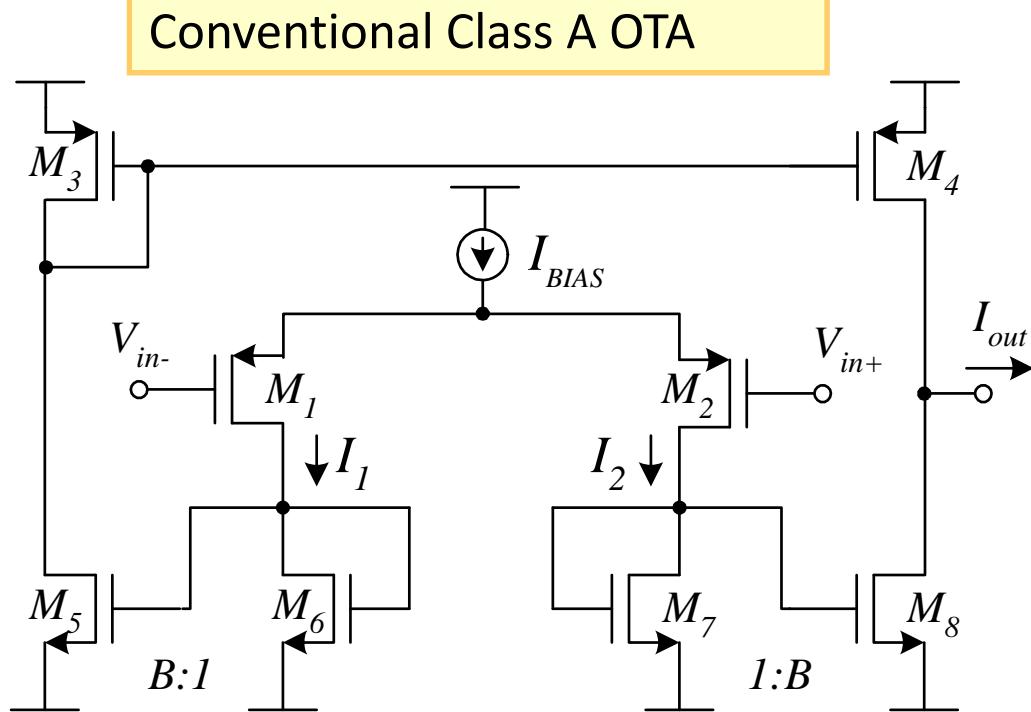
► **Objective:** Design cells for $V_{DD} < V_{DDmin}$ featuring Class-AB behavior

- Adaptive biasing+LCMFB = Super Class AB
- Improvements:
 - Slew rate
 - Gain-Bandwidth product
 - Current efficiency
- Applications
 - Low-voltage low-power SC circuits
 - Buffers for large load caps and testing

LFL: Basic Cells

Local Feedback Loops: Class-AB operation

► Objective: Design cells for $V_{DD} < V_{DDmin}$ featuring Class-AB behavior



Slew Rate: BI_{BIAS}/C_L

GB: $Bg_{m1,2}/(2\pi C_L)$

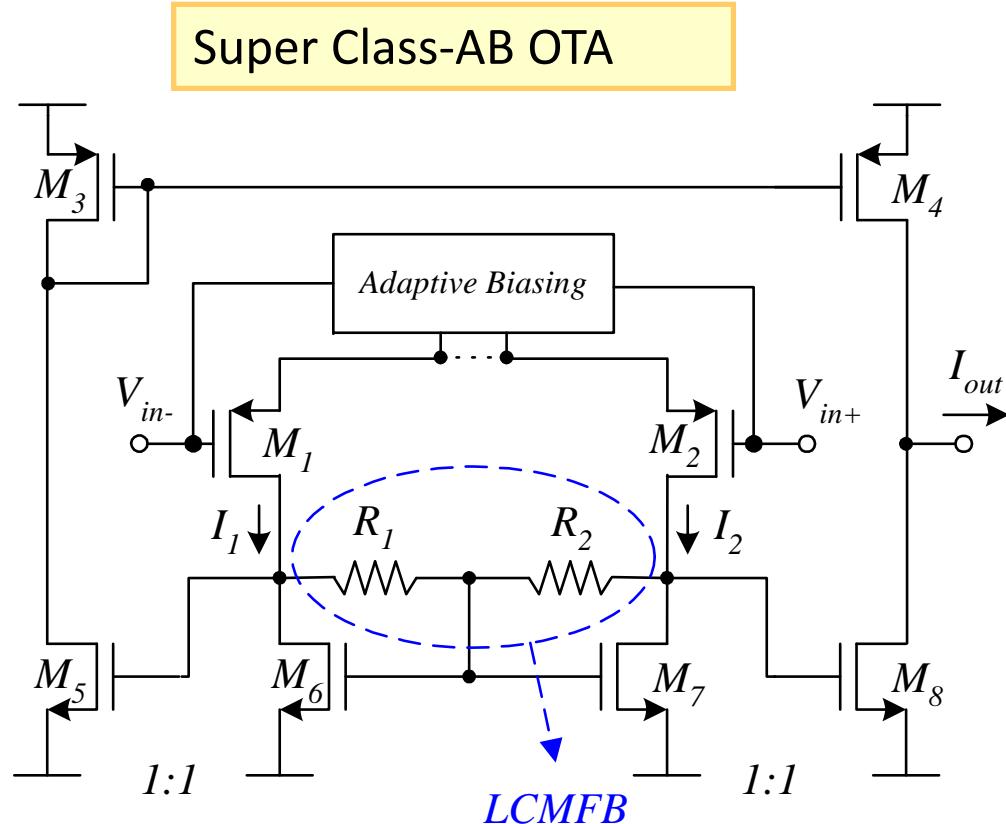
Current Efficiency:
 $B/(B+1)$

Larger B increases all this but also increases power consumption and decreases phase margin

LFL: Basic Cells

Local Feedback Loops: Class-AB operation

► Objective: Design cells for $V_{DD} < V_{DDmin}$ featuring Class-AB behavior

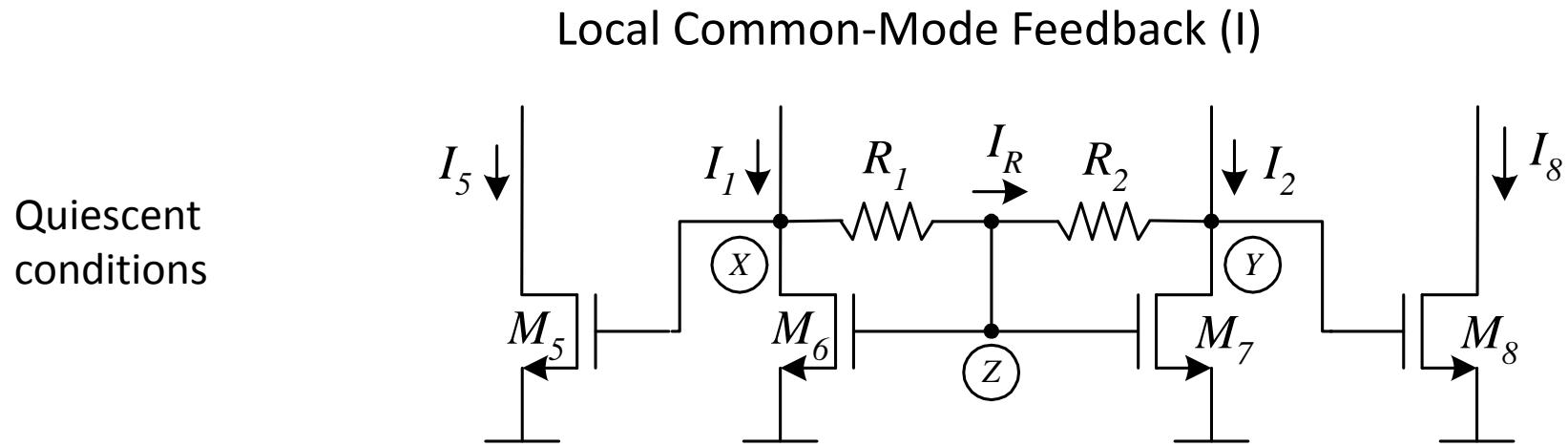


- Adpatative biasing:
 - ↑ Slew rate
- LCMFB:
 - ↑↑ Slew rate
 - ↑ GBW
 - ↑ Current
 - Efficiency

LFL: Basic Cells

Local Feedback Loops: Class-AB operation

► **Objective:** Design cells for $V_{DD} < V_{DDmin}$ featuring Class-AB behavior



$$V_X = V_Y = V_Z = V_{TH} + \sqrt{\frac{2I_B}{\beta_{6,7}}}$$

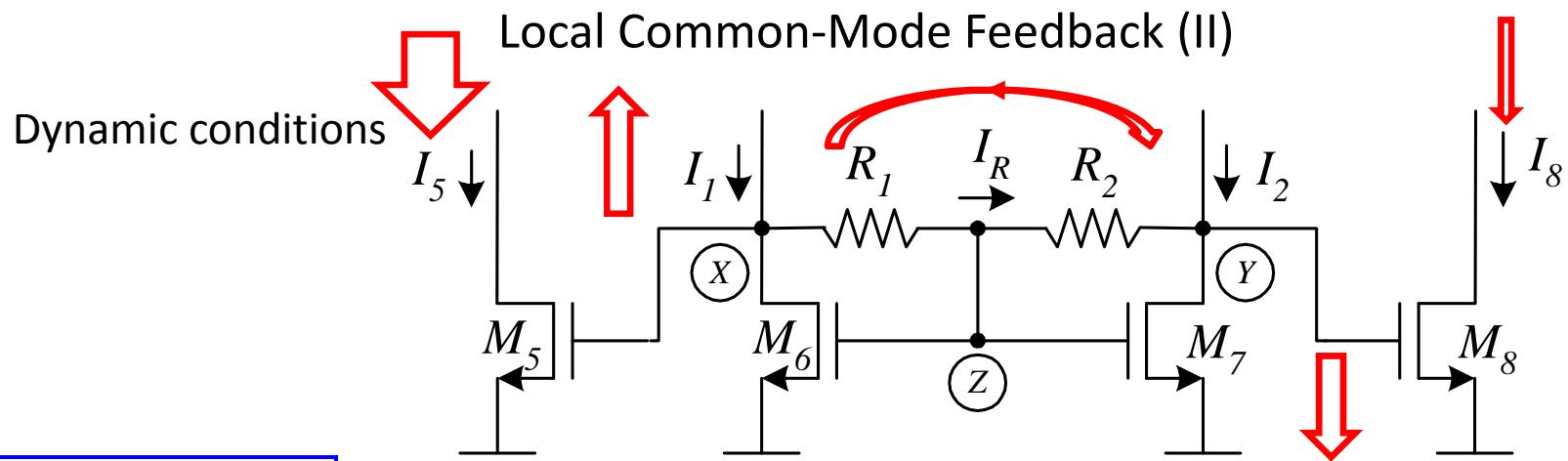
I_B : Quiescent value of I_1 and I_2

Low quiescent power consumption

LFL: Basic Cells

Local Feedback Loops: Class-AB operation

► **Objective:** Design cells for $V_{DD} < V_{DDmin}$ featuring Class-AB behavior



$$V_Z = V_{TH} + \sqrt{\frac{2I_{cm}}{\beta_{6,7}}}$$

$$V_X = V_Z + \frac{R_1 I_d}{2}$$

$$V_Y = V_Z - \frac{R_2 I_d}{2}$$

If $I_1 > I_2$:

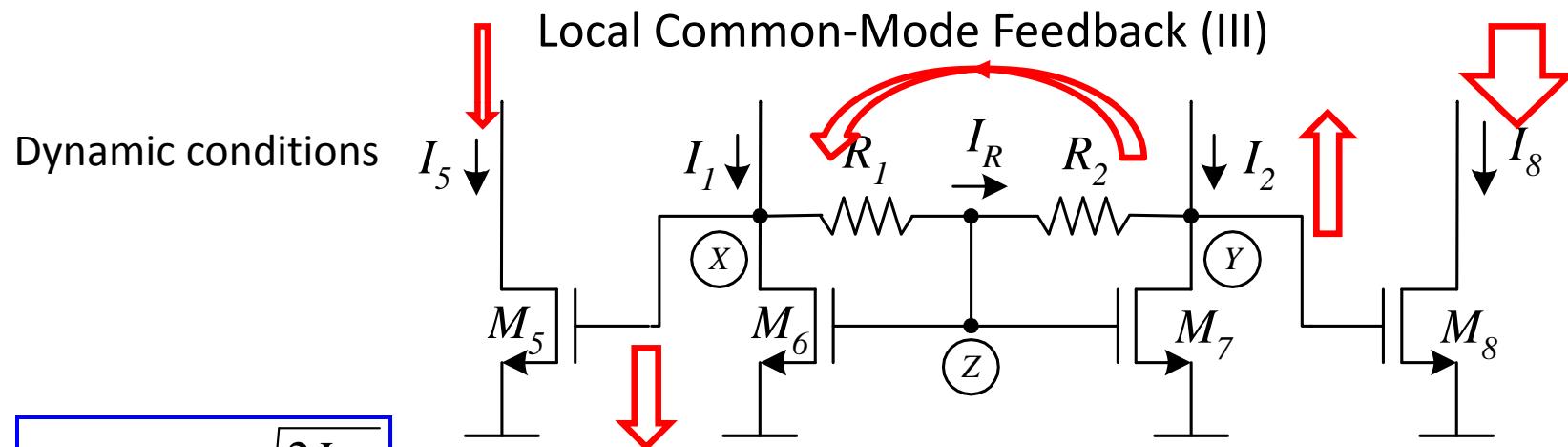
$$\left\{ \begin{array}{l} I_5 = \frac{\beta_5}{2} \left(\sqrt{\frac{2I_{cm}}{\beta_{6,7}}} + \frac{R_1 I_d}{2} \right)^2 \\ I_{out} = I_5 - I_8 \approx I_5 \end{array} \right.$$

where $I_{cm} = (I_1 + I_2)/2$ and $I_d = I_1 - I_2$

LFL: Basic Cells

Local Feedback Loops: Class-AB operation

► **Objective:** Design cells for $V_{DD} < V_{DD\min}$ featuring Class-AB behavior



$$V_Z = V_{TH} + \sqrt{\frac{2I_{cm}}{\beta_{6,7}}}$$

$$V_X = V_Z + \frac{R_1 I_d}{2}$$

$$V_Y = V_Z - \frac{R_2 I_d}{2}$$

If $I_1 < I_2$:

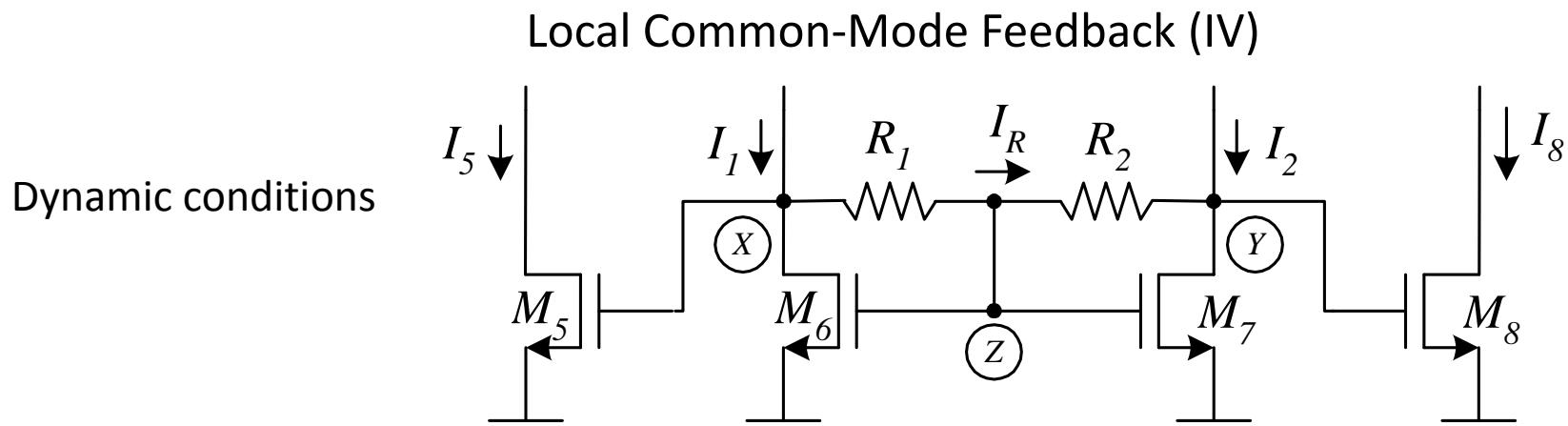
$$\begin{cases} I_8 = \frac{\beta_8}{2} \left(\sqrt{\frac{2I_{cm}}{\beta_{6,7}}} - \frac{R_2 I_d}{2} \right)^2 \\ I_{out} = I_5 - I_8 \approx -I_8 \end{cases}$$

where $I_{cm} = (I_1 + I_2)/2$ and $I_d = I_1 - I_2$

LFL: Basic Cells

Local Feedback Loops: Class-AB operation

► **Objective:** Design cells for $V_{DD} < V_{DDmin}$ featuring Class-AB behavior



General expression for $I_1 \neq I_2$:

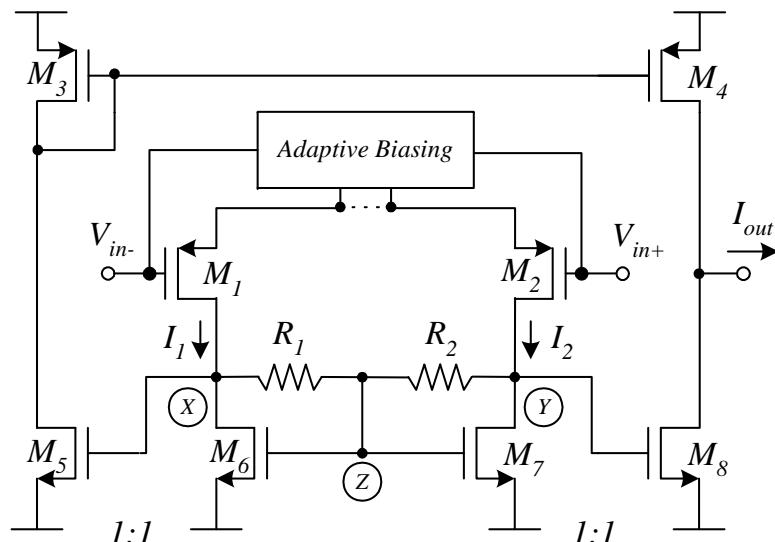
$$I_{out} = I_5 - I_8 \approx \pm \frac{\beta_{5,8}}{2} \left(\sqrt{\frac{2I_{cm}}{\beta_{6,7}}} + \frac{R_{1,2}|I_d|}{2} \right)^2$$

Quadratic boosting of differential current I_d

LFL: Basic Cells

Local Feedback Loops: Class-AB operation

► **Objective:** Design cells for $V_{DD} < V_{DD\min}$ featuring Class-AB behavior



Phase margin:

Adaptive Biasing+LCMFB

GB product:

$$GB = \frac{kg_{m1,2}g_{m5,8}R_{X,Y}}{2\pi C_L}$$

⇒ Increase of $kg_{m5,8}R_{X,Y}$

Large-signal output current:

$$I_{out} \approx \pm \frac{\beta_{5,8}}{2} \left(\sqrt{\frac{\beta_{1,2}}{\beta_{6,7}}} |V_{id}| + \frac{R_{1,2}\beta_{1,2}}{4} V_{id}^2 \right)^2$$

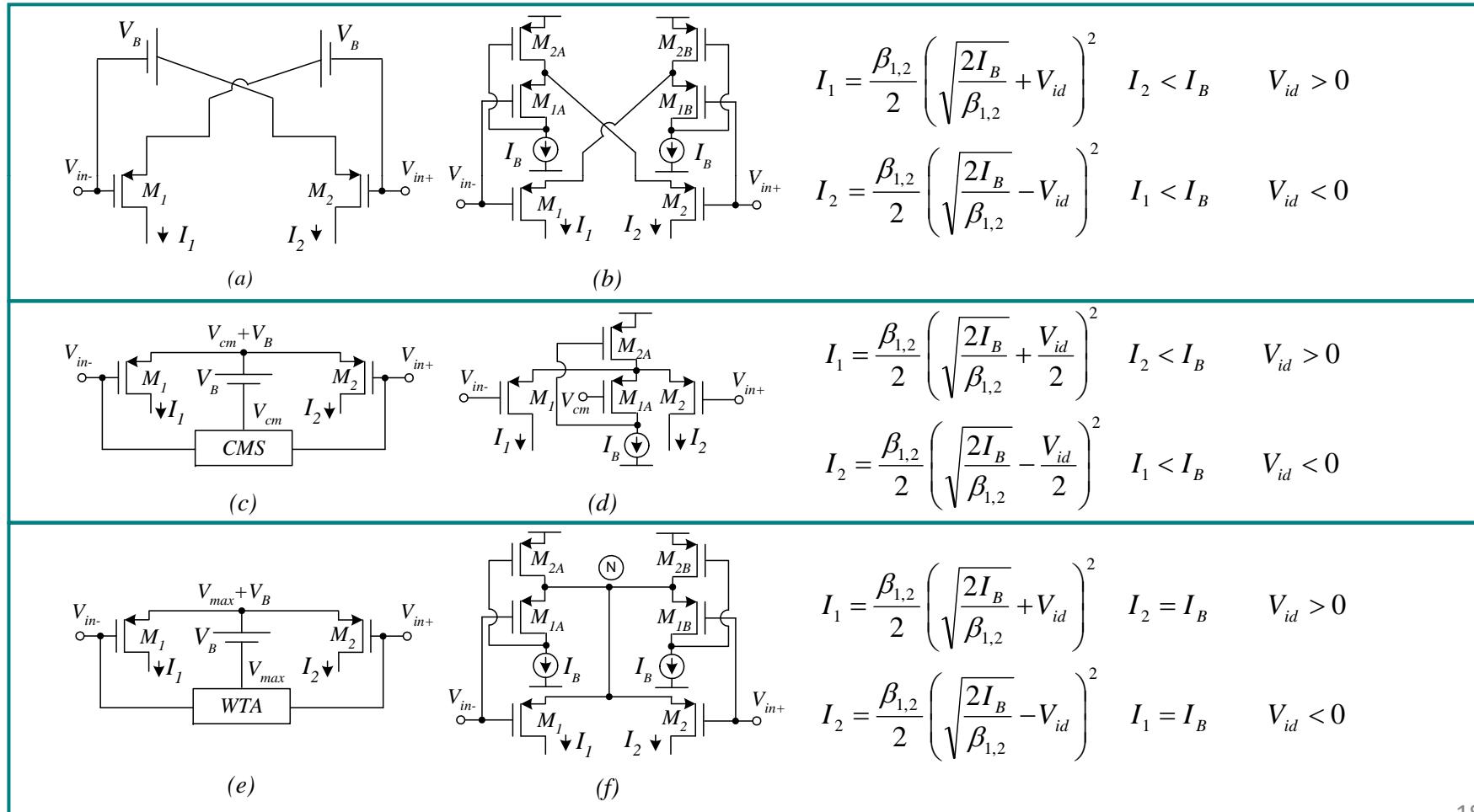
$$PM \approx 90^\circ - arctg \left(\frac{GBW}{f_{X,Y}} \right) \approx 90^\circ - arctg \left[kg_{m1,2}g_{m5,8} (R_{1,2} \parallel r_{o6,7} \parallel r_{o1,2})^2 \frac{C_{GS5,8}}{C_L} \right]$$

High SR with low $R_{1,2} \Rightarrow$ stability

LFL: Basic Cells

Local Feedback Loops: Class-AB operation

Adaptive Biasing of Input Pair: SI

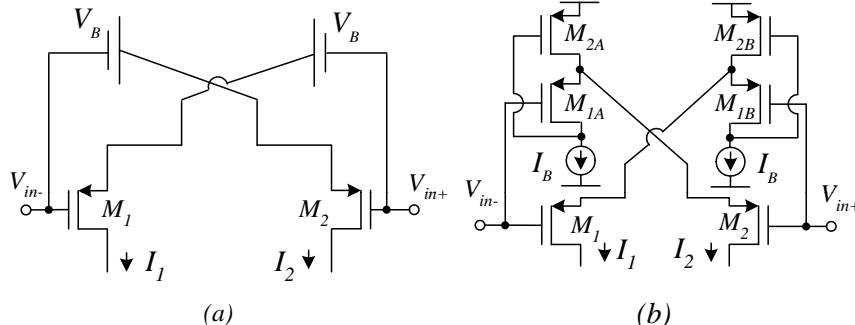


Strong inversion: Quadratic boosting of V_{id} not limited by I_B

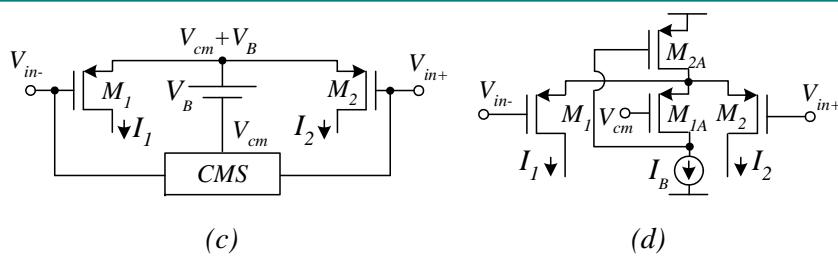
LFL: Basic Cells

Local Feedback Loops: Class-AB operation

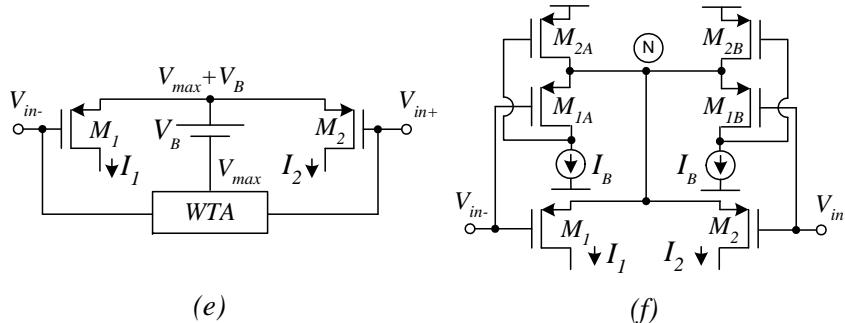
Adaptive Biasing of Input Pair: WI



$$I_1 = I_B e^{\frac{V_{id}}{nU_T}} \quad I_2 = I_B e^{-\frac{V_{id}}{nU_T}}$$



$$I_1 = I_B e^{\frac{V_{id}}{2nU_T}} \quad I_2 = I_B e^{-\frac{V_{id}}{2nU_T}}$$

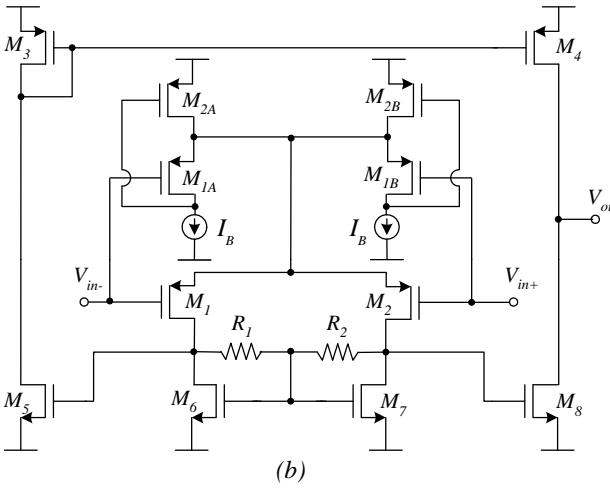
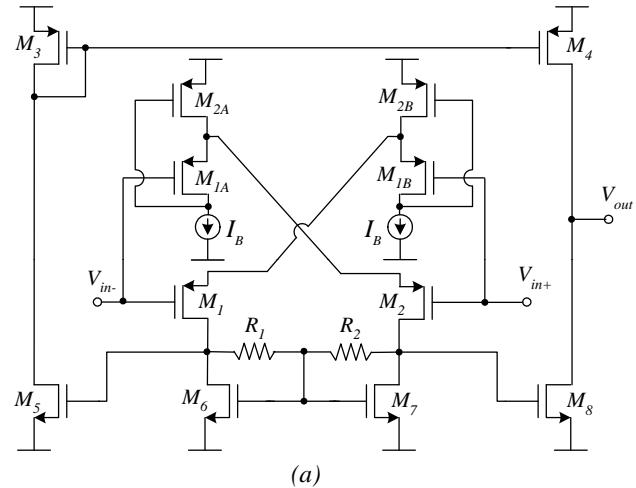


$$I_1 = \max\left(I_B e^{\frac{V_{id}}{nU_T}}, I_B\right) \quad I_2 = \max\left(I_B e^{-\frac{V_{id}}{nU_T}}, I_B\right)$$

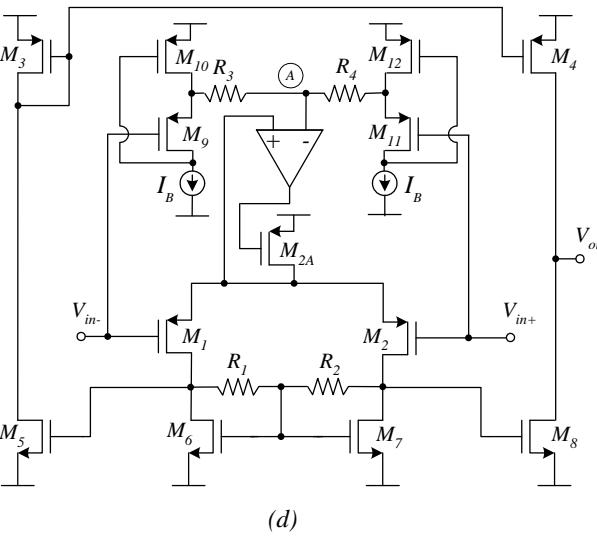
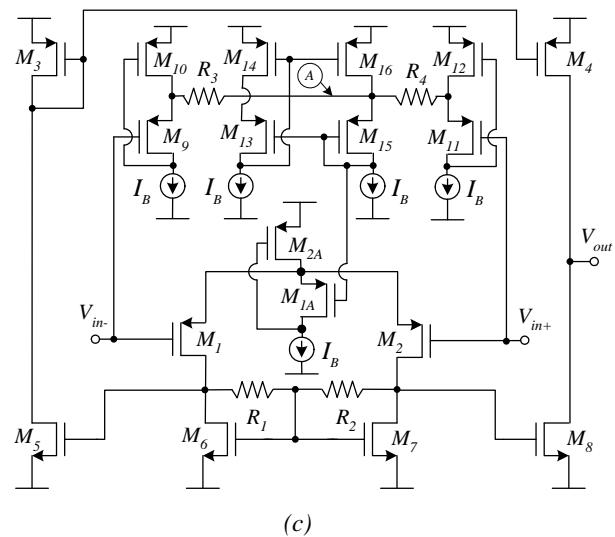
Weak inversion: Exponential boosting of V_{id} not limited by I_B

LFL: Basic Cells

Local Feedback Loops: Class-AB operation



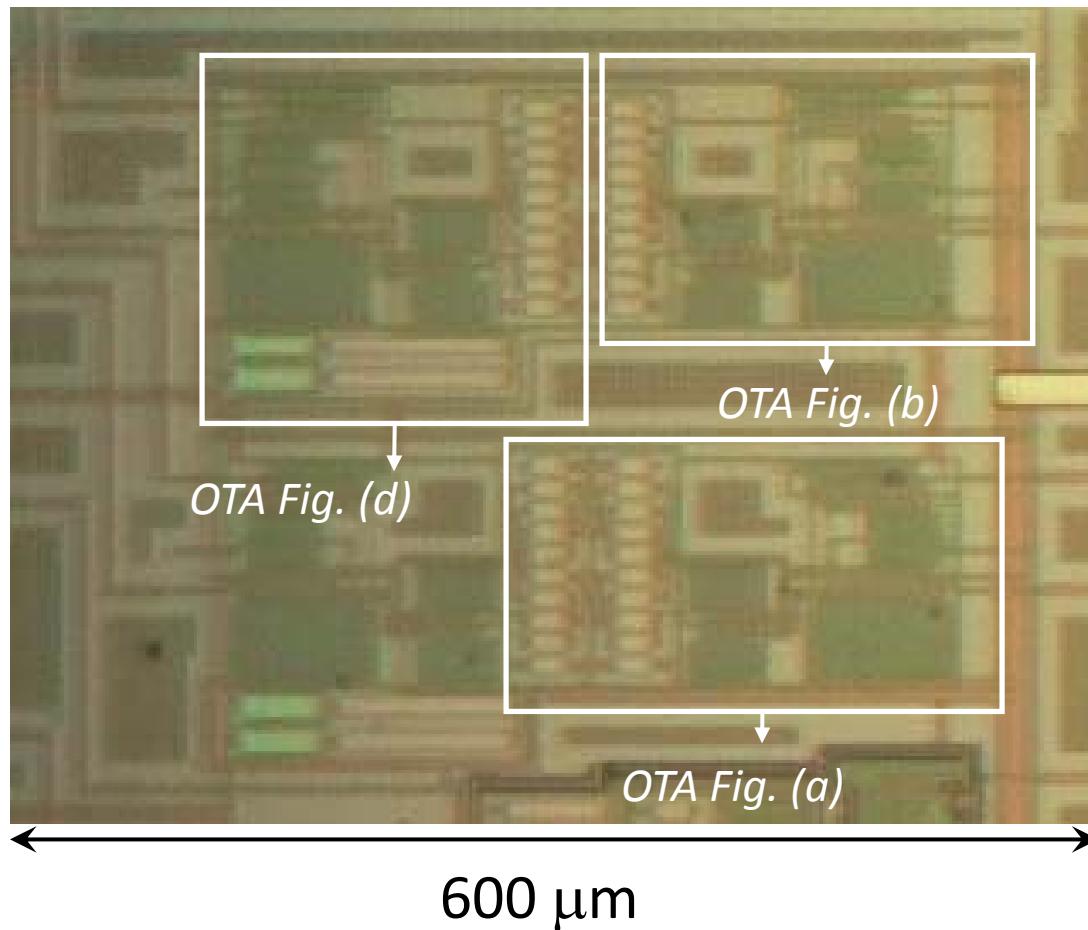
**Super Class AB
OTA Topologies**



LFL: Basic Cells

Local Feedback Loops: Class-AB operation

Measurement Results (I)



Technology:

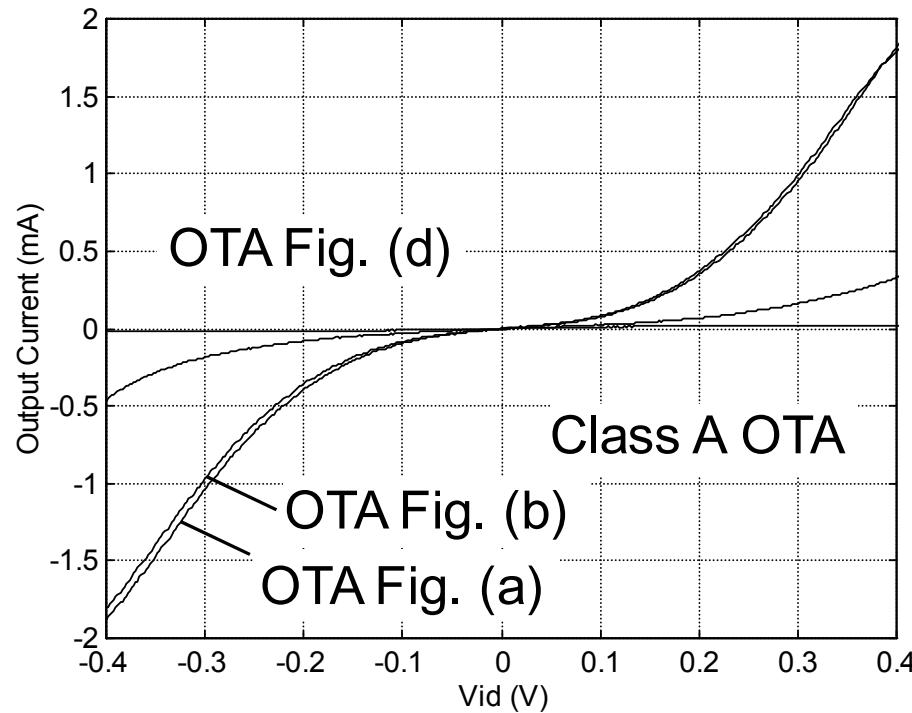
- ✓ 0.5 μm CMOS
- ✓ Double Poly
- ✓ $V_{THP} \approx -0.96V$
- ✓ $V_{THN} \approx 0.67V$

Meas. conditions:

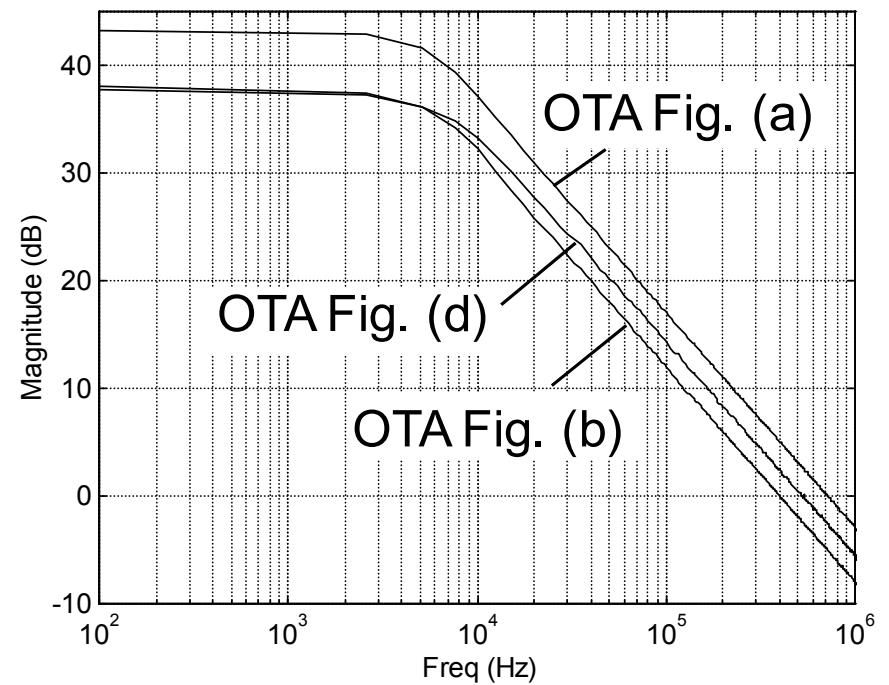
- ✓ $V_{DD} = -V_{SS} = 1 V$
- ✓ $I_B = 10 \mu A$
- ✓ $C_L = 80 pF$

LFL: Basic Cells

Local Feedback Loops: Class-AB operation



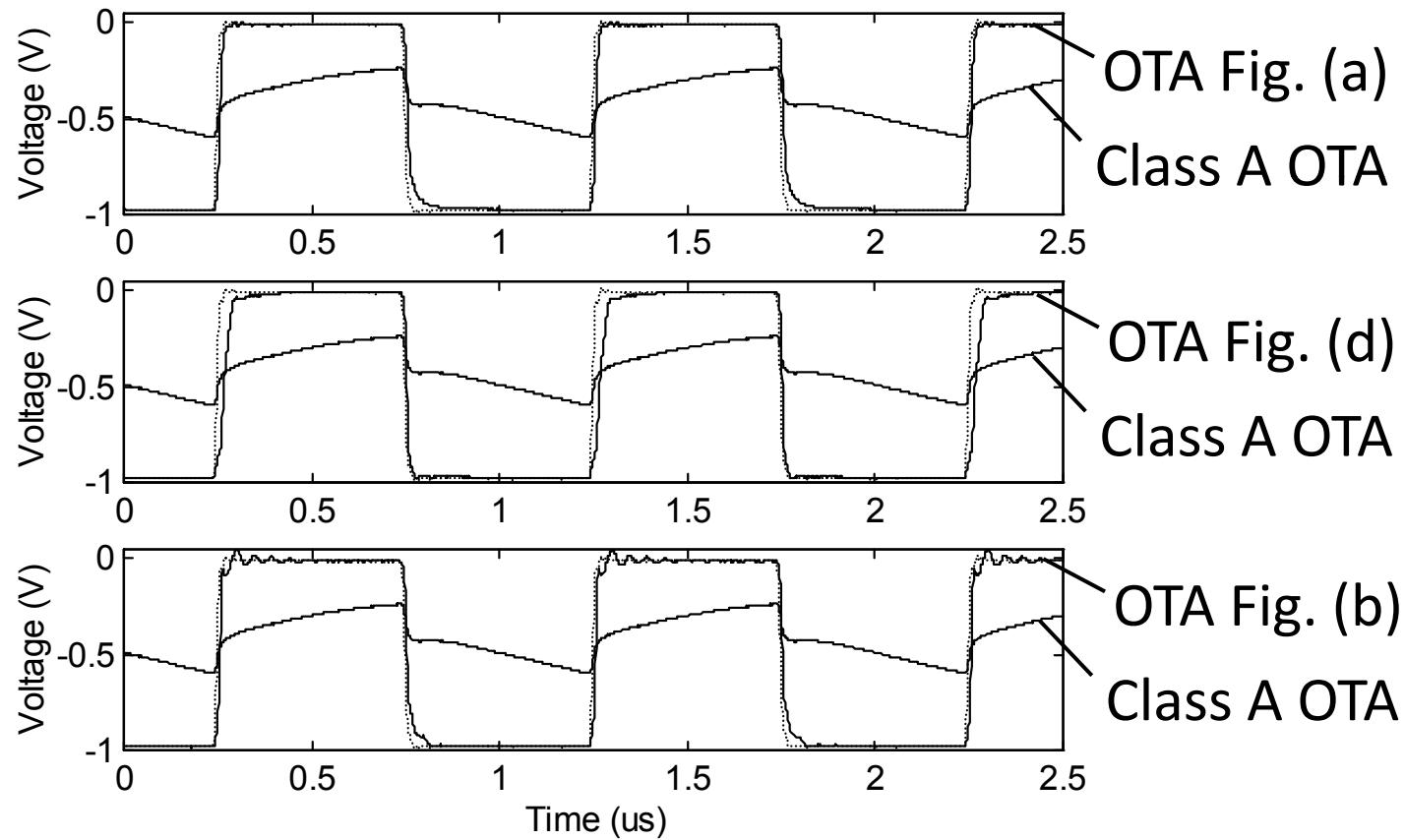
Measured dc output
characteristics of the OTAs



Measured open-loop frequency
response of the OTAs

LFL: Basic Cells

Local Feedback Loops: Class-AB operation



Transient response of the OTAs in unity-gain configuration

LFL: Basic Cells

Local Feedback Loops: Super Class-AB operation

PARAMETER	Class A OTA	OTA Fig. 3(a)	OTA Fig. 3(b)	OTA Fig. 3(d)
Slew Rate (positive)	0.35 V/ μ s	100 V/ μ s	92 V/ μ s	42 V/ μ s
Slew Rate (negative)	-0.4 V/ μ s	-78 V/ μ s	-76 V/ μ s	-80 V/ μ s
Pos. settling (1%)	3.1 μ s	29 ns	66 ns	100 ns
Neg. settling (1%)	3.6 μ s	57 ns	62 ns	33 ns
GBW	200 kHz	725 kHz	410 kHz	470 kHz
Equ. Input Noise (1 MHz)	223 μ V _{rms}	230 μ V _{rms}	230 μ V _{rms}	252 μ V _{rms}
THD @ 100 kHz, 0.9V _{pp}	-40 dB	-56 dB	-43 dB	-41 dB
Dynamic range	63 dB	66 dB	63.7 dB	62.5 dB
DC gain	30 dB	43 dB	37.5 dB	37.5 dB
CMRR	54 dB	68 dB	70 dB	69 dB
PSRR+ (dc)	48 dB	55 dB	50 dB	57 dB
PSRR- (dc)	44 dB	58 dB	53 dB	46 dB
Static power consumption	80 μ W	120 μ W	120 μ W	140 μ W
Die area	0.011 mm ²	0.024 mm ²	0.024 mm ²	0.042 mm ²

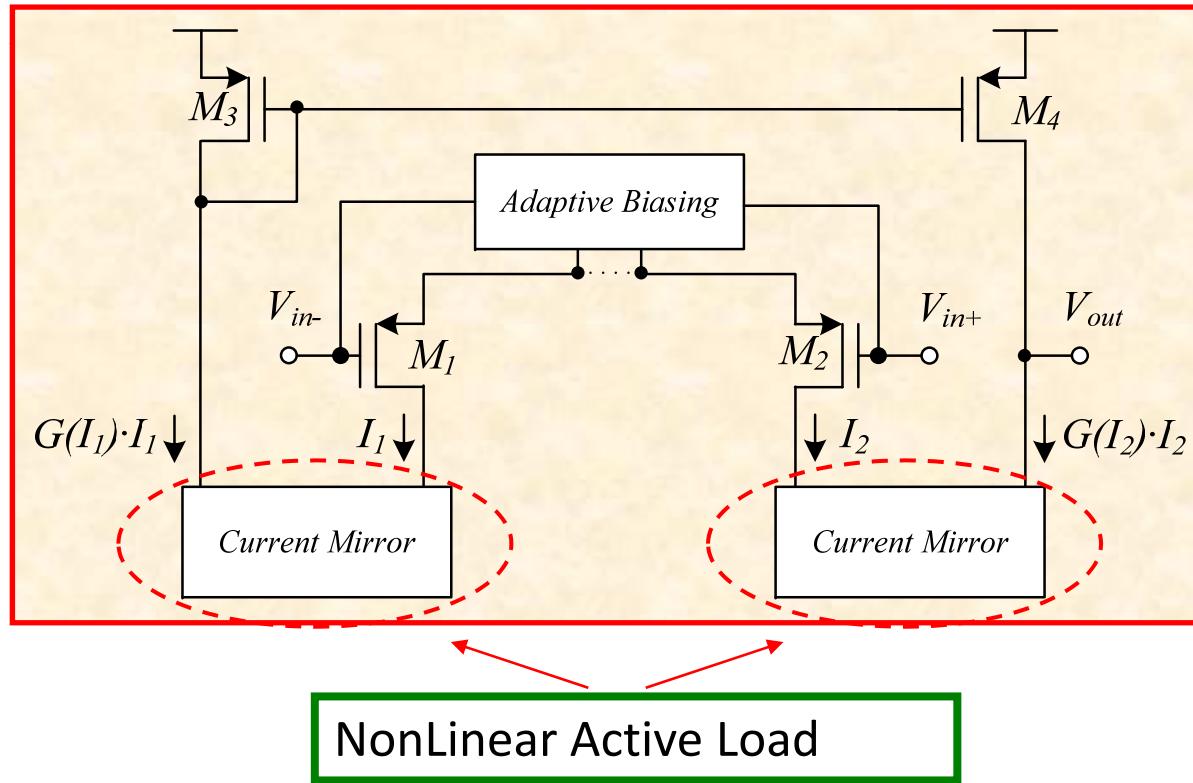
Performance parameters of the OTAs

Antonio J. López Martín, Sushmita Baswa, Jaime Ramírez Angulo, R.G. Carvajal, "Low-Voltage Power-Efficient Super Class AB CMOS OTA Cells with Very High Slew Rate and Power Efficiency," [IEEE Journal of Solid-State Circuits](#), vol. 40, no. 5, pp. 1068-1077, Mayo de 2005

LFL: Basic Cells

Local Feedback Loops: Super Class-AB operation

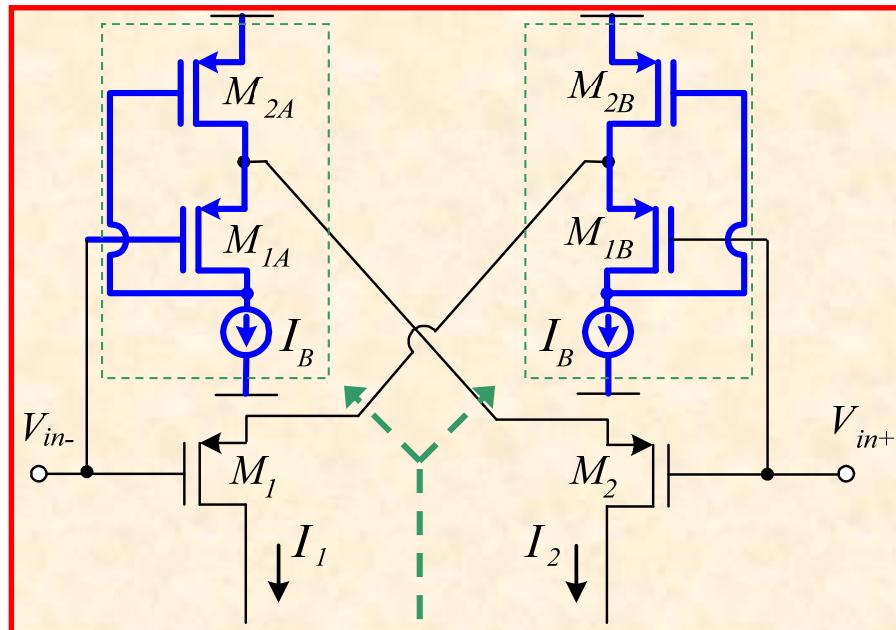
Proposed Circuit Topology



LFL: Basic Cells

Local Feedback Loops: Super Class-AB operation

Class-AB Input Stage

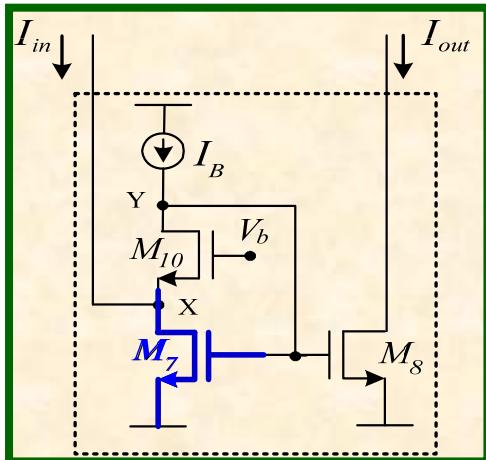


Local Feedback

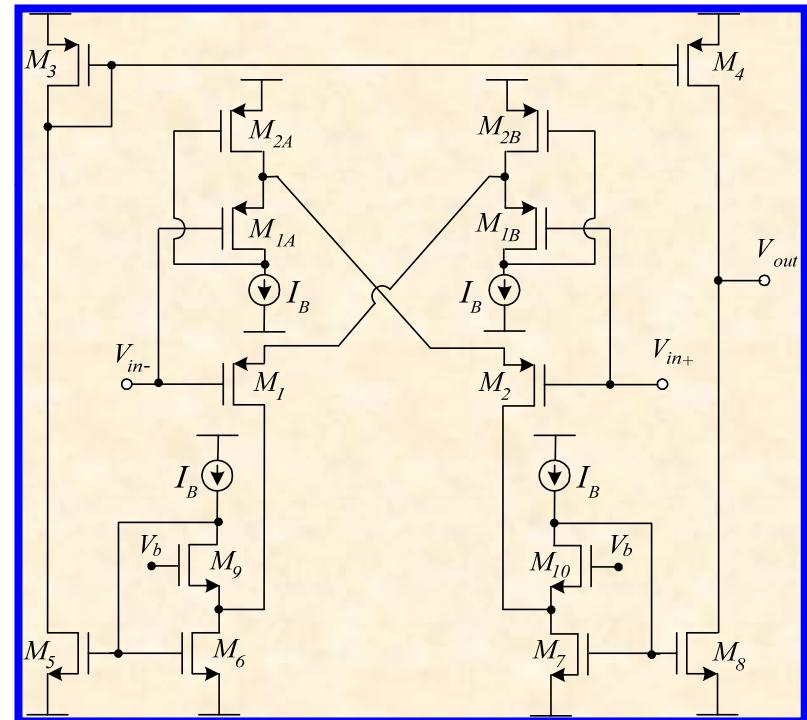
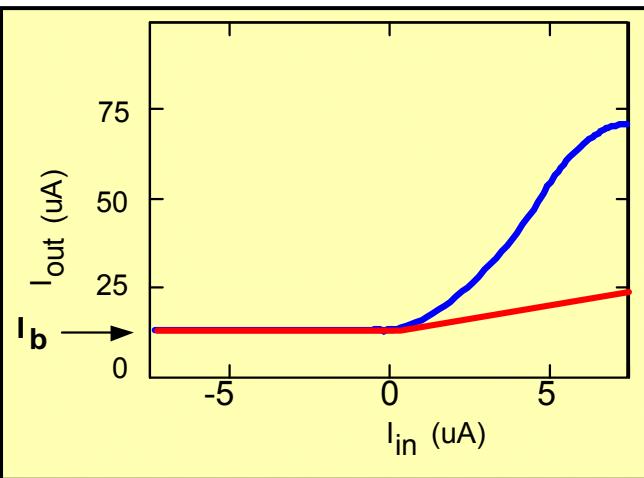
$$I_1 = \frac{\beta_{1,2}}{2} \left(\sqrt{\frac{2I_B}{\beta_{1,2}}} + V_{id} \right)^2 \quad I_2 < I_B \quad V_{id} > 0$$
$$I_2 = \frac{\beta_{1,2}}{2} \left(\sqrt{\frac{2I_B}{\beta_{1,2}}} - V_{id} \right)^2 \quad I_1 < I_B \quad V_{id} < 0$$

LFL: Basic Cells

Local Feedback Loops: Super Class-AB operation



Class AB current mirror

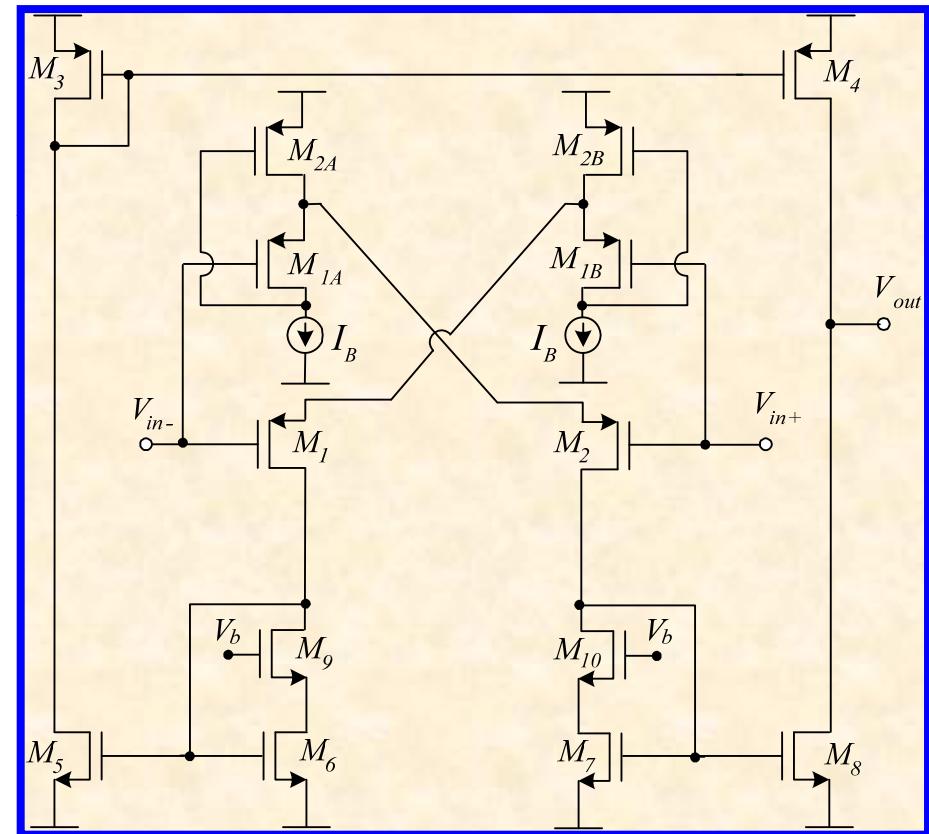
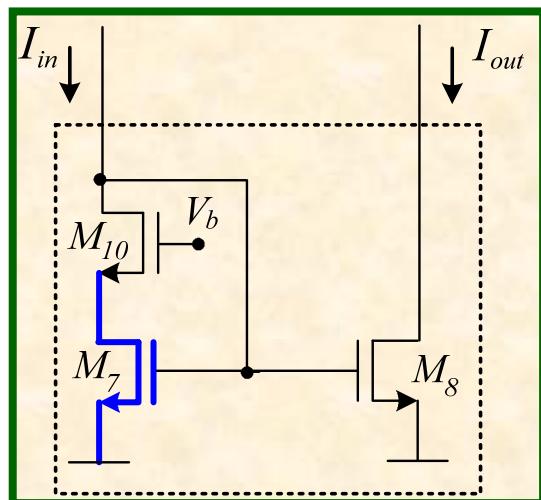


1st proposed OTA

LFL: Basic Cells

Local Feedback Loops: Super Class-AB operation

Non-linear current mirror

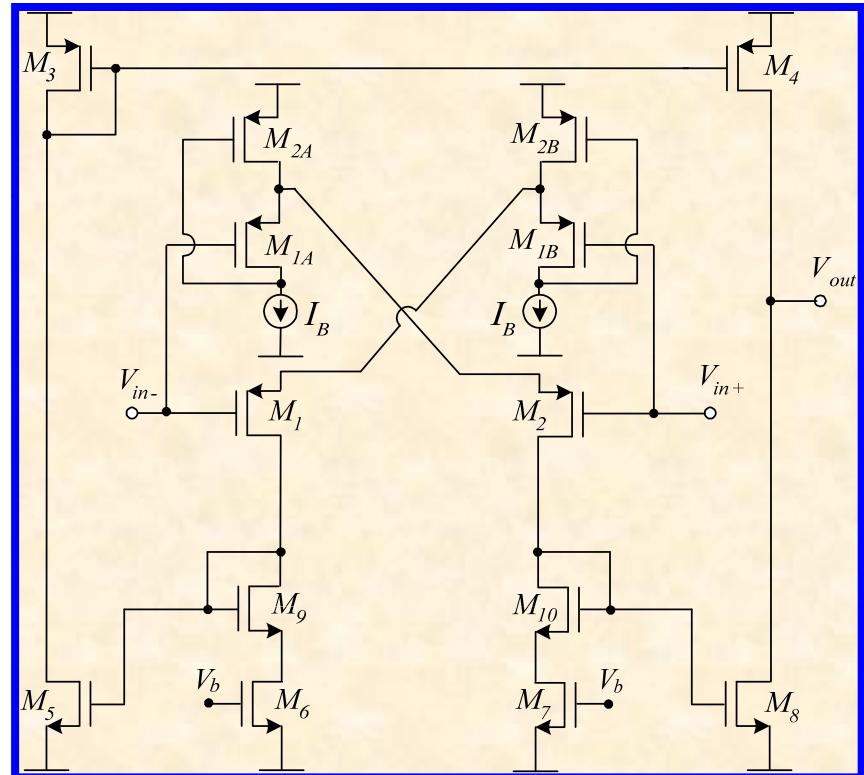
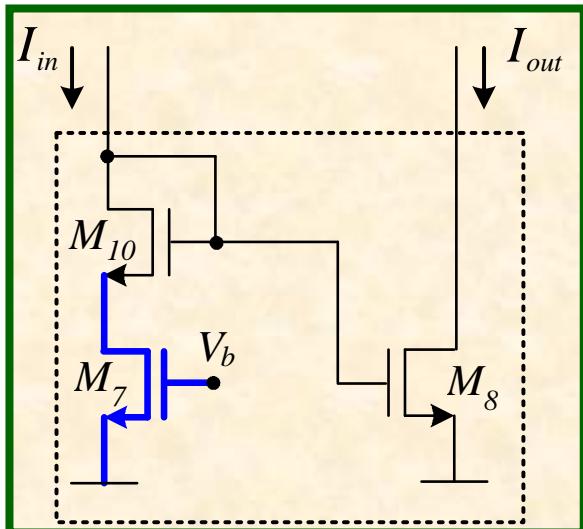


2nd proposed OTA

LFL: Basic Cells

Local Feedback Loops: Super Class-AB operation

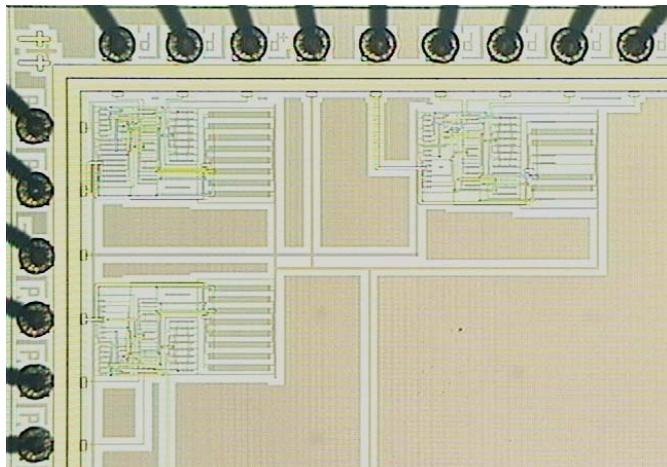
Non-linear source degenerated current mirror



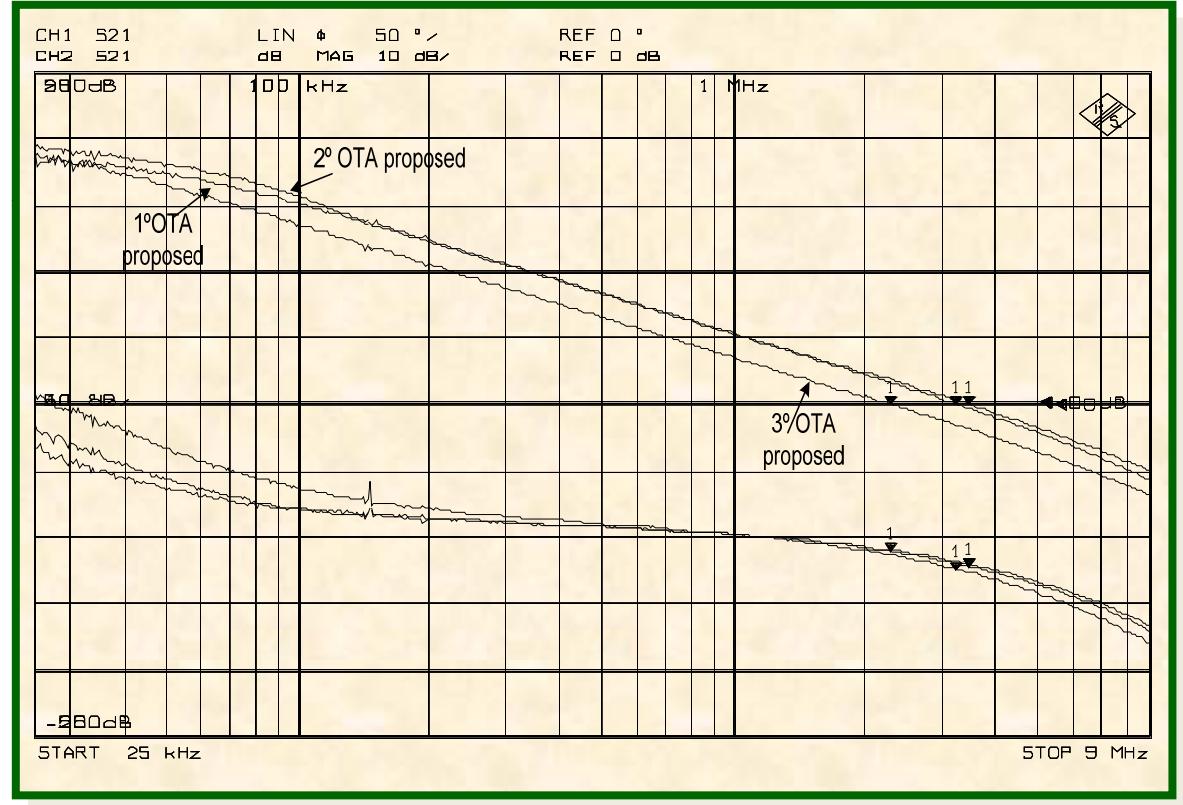
3rd proposed OTA

LFL: Basic Cells

Local Feedback Loops: Super Class-AB operation



$V_{DD} = \pm 1V$
 $I_B = 10\mu A$
 $C_L = 80pF$

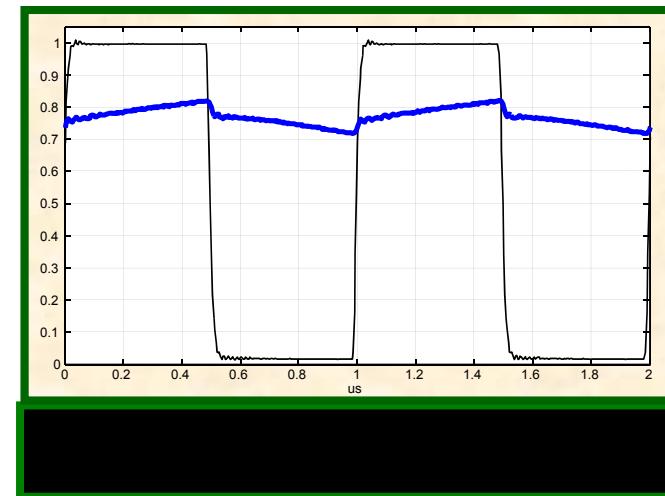
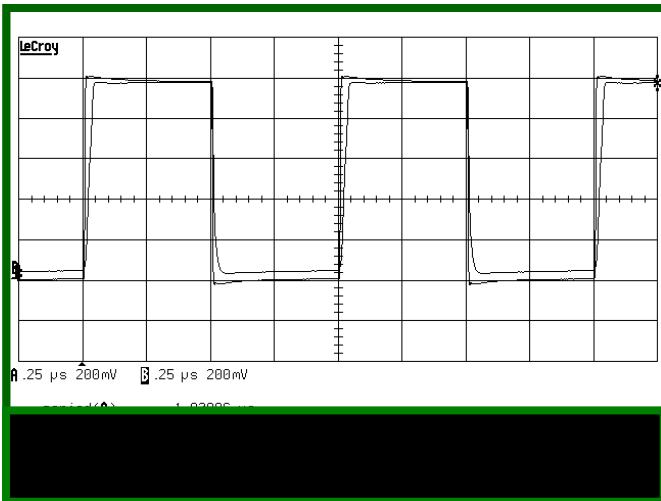
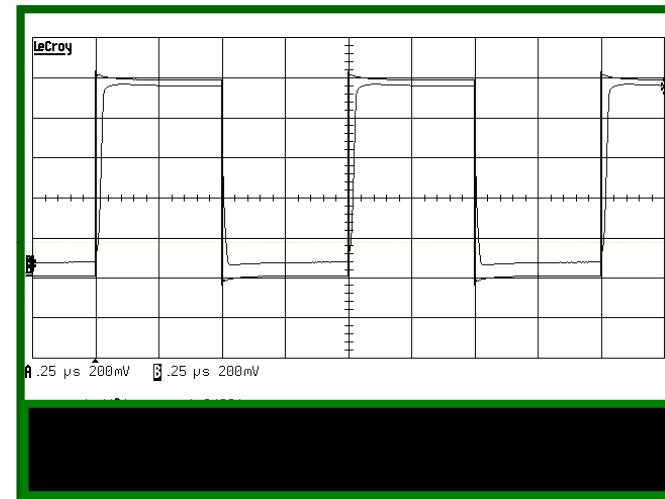
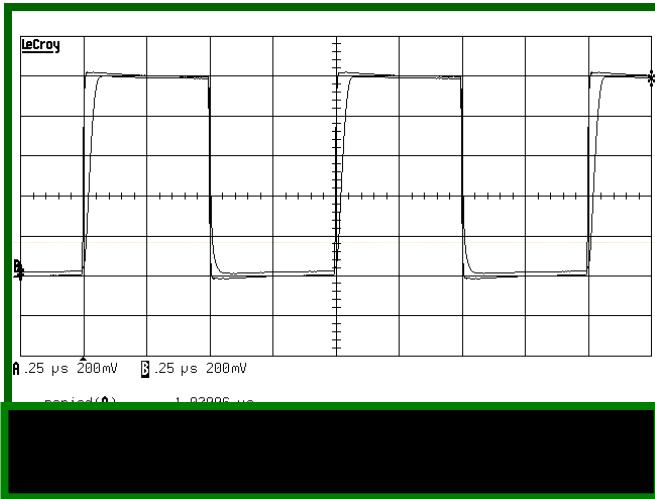


AMI 0.5 μm CMOS Technology

Frequency Response

LFL: Basic Cells

Local Feedback Loops: Super Class-AB operation



LFL: Basic Cells

Local Feedback Loops: Super Class-AB operation

Measured performance of the fabricated OTAs

Slew Rate (positive)	0.35 V/ μ s	10 V/ μ s	20 V/ μ s	14 V/ μ s
Slew Rate (negative)	-0.4 V/ μ s	-15 V/ μ s	-54 V/ μ s	-28 V/ μ s
GBW	200 kHz	3.27 MHz	3.46 MHz	2.3 MHz
Static power consumption	80 μ W	220 μ W	140 μ W	140 μ W